Trench Power MOSFET

20 V, 4.0 A, Single N-Channel, SC-88

Features

- Leading Trench Technology for Low R_{DS(ON)} Extending Battery Life
- Fast Switching for Increased Circuit Efficiency
- SC-88 Small Outline (2 x 2 mm) for Maximum Circuit Board Utilization, Same as SC-70-6
- These are Pb–Free Devices

Applications

- DC–DC Conversion
- Low Side Load Switch
- Cell Phones, Computing, Digital Cameras, MP3s and PDAs

MAXIMUM RATINGS (T_J = 25° C unless otherwise stated)

Param	Symbol	Value	Unit			
Drain-to-Source Voltage	V _{DSS}	20	V			
Gate-to-Source Voltage	V _{GS}	±8.0	V			
Continuous Drain	Steady	T _A = 25 °C	۱ _D	3.2	А	
Current (Note 1)	State	T _A = 85 °C		2.3		
	t ≤ 5 s	$T_A = 25 \ ^\circ C$		4.0		
Power Dissipation (Note 1) Steady		T _A = 25 °C	PD	1.0	W	
Pulsed Drain Current	I _{DM}	10	А			
Operating Junction and S	T _J , T _{STG}	–55 to 150	°C			
Source Current (Body Di	۱ _S	1.6	А			
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			ΤL	260	°C	

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State	$R_{\theta JA}$	125	°C/W
Junction-to-Ambient – t \leq 5 s	$R_{\theta JA}$	80	
Junction-to-Lead - Steady State	R_{\thetaJL}	45	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq pad size

(Cu area = 1.127 in sq [1 oz] including traces).

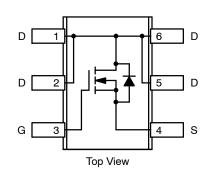


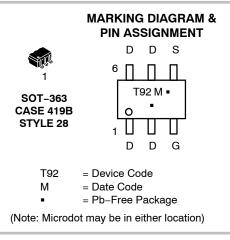
ON Semiconductor®

http://onsemi.com

V _{(BR)DSS}	R _{DS(on)} Typ	I _D Max	
20 V	45 mΩ @ 4.5 V		
	55 mΩ @ 2.5 V	4.0 A	
	70 mΩ @ 1.8 V		







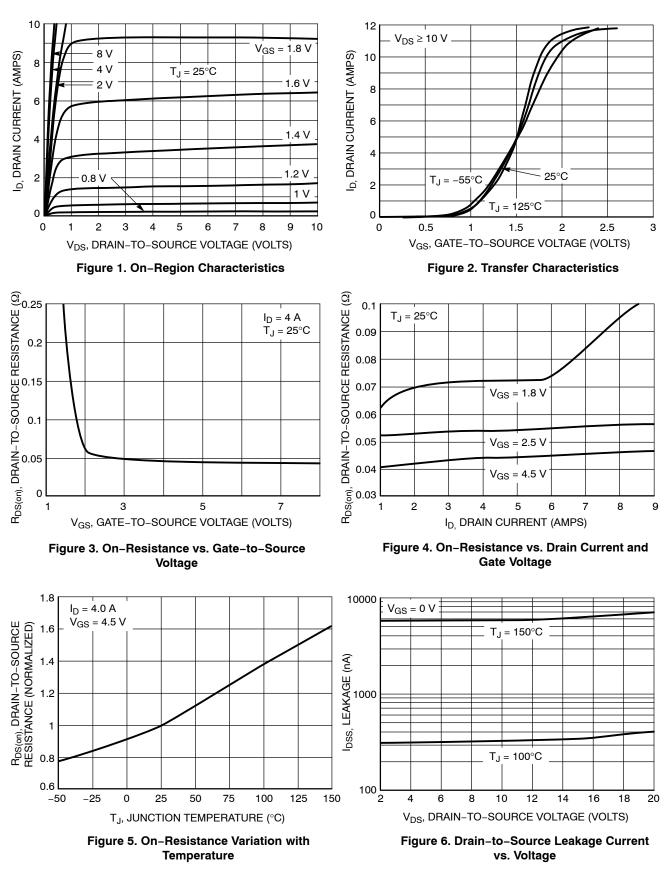
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise stated)

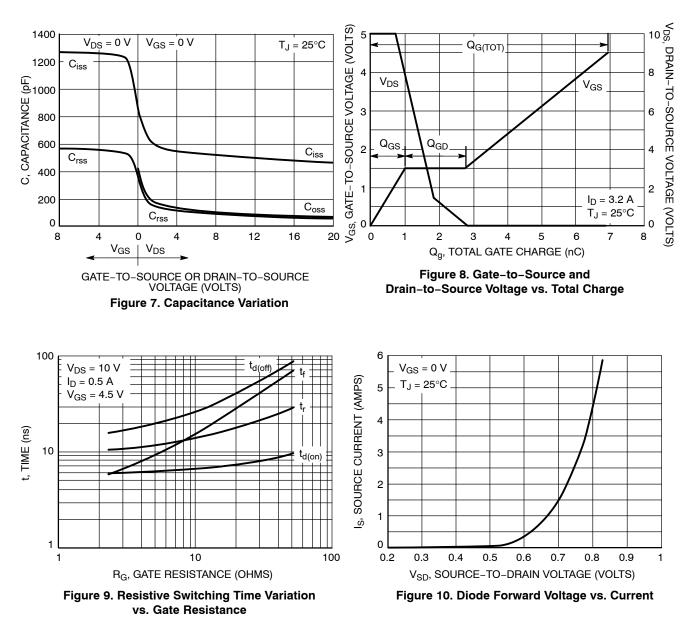
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I _D = 250 µA		20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	V_{GS} = 0 V, I _D = 250 μ A			12		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 16 V	$T_J = 25^{\circ}C$			1.0	μΑ
			$T_J = 85^{\circ}C$			5.0	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _G	_S = ±8.0 V			±100	nA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V _{GS(TH)}			0.40		1.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J	V_{GS} = V_{DS} , I_D = 250 μ A			-4.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	R _{DS(on)} V _{GS} = 4.5 V, I _D = 4.0 A			45	60	mΩ
		V _{GS} = 2.5 V,	I _D = 3.6 A		55	70	
		V _{GS} = 1.8 V,	I _D = 2.0 A		70	85	
Forward Transconductance	9 FS	V _{GS} = 10 V, I _D = 3.2 A			9.0		S
CHARGES AND CAPACITANCES		•			•		•
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 10 V			500		pF
Output Capacitance	C _{OSS}				75		
Reverse Transfer Capacitance	C _{RSS}	•DS -			60		1
Total Gate Charge	Q _{G(TOT)}				6.9	15	nC
Gate-to-Source Charge	Q _{GS}	V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 3.2 A			1.0		1
Gate-to-Drain Charge	Q _{GD}				1.8		
SWITCHING CHARACTERISTICS (No	te 3)						
Turn-On Delay Time	t _{d(on)}				6.0	15	ns
Rise Time	t _r	$V_{co} = 4.5 V V$	'nn = 10 V		12	25	
Turn-Off Delay Time	t _{d(off)}	V_{GS} = 4.5 V, V_{DD} = 10 V, I _D = 0.5 A, R _G = 6.0 Ω			21	45	
Fall Time	t _f	1	F		11	25	
DRAIN-SOURCE DIODE CHARACTE	RISTICS						
Forward Diode Voltage	V _{SD}	V _{GS} =0 V, I _S = 1.6 A	T _J = 25°C		0.7	1.0	V
Reverse Recovery Time	t _{RR}		·		15		ns
Charge Time	T _a	V_{GS} = 0 V, dI _S /dt = 100 A/µs, I _S = 1.6 A			12		-
Discharge Time	T _b				3.0		
Reverse Recovery Charge	Q _{RR}				5.0		nC

Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
Switching characteristics are independent of operating junction temperatures.



TYPICAL PERFORMANCE CURVES (T_J = 25° C unless otherwise noted)

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)



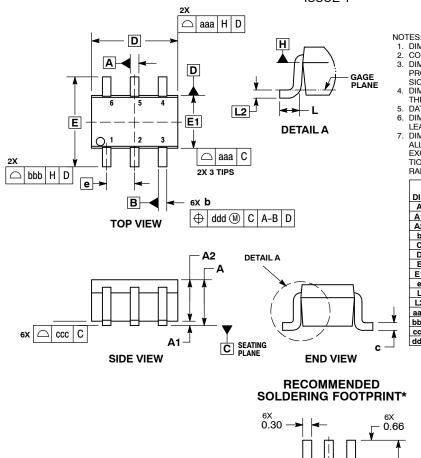
ORDERING INFORMATION

Device	Package	Shipping [†]	
NTJS3157NT1G	SC-88 (Pb-Free)	3000 Tape & Reel	
NTJS3157NT2G	SC-88 (Pb-Free)	3000 Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y



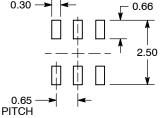
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- CONTROLLING DIMENSION: MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRU-SIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS D AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALL OWABLE DAMBAR PROTRUSION SHALL BE 0.08 ATOTAL IN

- ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
Е	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10				0.004	

STYLE 28: PIN 1. DRAIN 2. DRAIN

- 3. GATE 4. SOURCE 5 6 DRAIN
- DRAIN



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SciLLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SciLLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights or the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implexition the body or other application is support or surgical life or for any other application is postemic intended to support or surgical life or for any other application specifical parameters as the information and specifical parameters application is purport. surgical input of the body, or other applications intended to support or sustain life, or for any other application in which the SCILLC product sud create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application. Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all daims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly or indirectly any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC reader design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative